Geometry-assisted topological transitions in spin interferometry

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We identify a series of topological transitions occurring in electronic spin transport when manipulating spin-guiding fields controlled by the geometric shape of mesoscopic interferometers. They manifest as distinct inversions of the interference pattern in quantum conductance experiments. We establish that Rashba square loops develop weak-(anti)localization transitions (absent in other geometries as Rashba ring loops) as an in-plane Zeeman field is applied. These transitions, boosted by non-adiabatic spin scattering, prove to have a topological interpretation in terms of winding numbers characterizing the structure of spin modes in the Bloch sphere.
Spin-orbit (SO) interaction emerges as a vector potential leading to a momentum-dependent magnetic texture that governs the evolution of itinerant spins in mesoscopic systems [1]. The resulting spin dynamics can exhibit a series of geometric and topological attributes of significant interest as the Aharonov-Casher (AC) effect [2], the electromagnetic dual of the Aharonov-Bohm (AB) effect [3]. Moreover, Berry showed that quantum states undergoing an adiabatic cyclic evolution acquire a phase factor of geometric nature with topological properties [4]. The concept of Berry phase is applied to topological quantum phenomena in various research fields such as optical and materials systems [5]. Recently, on/off Berry phase switch has been demonstrated in graphene resonators [6]. An elementary example is provided by mesoscopic rings subject to radial or crown-like magnetic textures, where Berry phases manifest as effective spin-dependent magnetic fluxes with consequences on quantum interference of spin carriers [7]- [14] recalling the AB effect. Topological transitions on the SO Berry phase were first discussed by Lyanda-Geller [15] by introducing an in-plane Zeeman field in a ring-shaped Rashba SO spin interferometer. However, in this setup the adiabatic condition cannot be satisfied near the transition point since the in-plane magnetic field produces a local cancellation of the effective Rashba SO field. Hence, a more sophisticated approach is required. We have shown that a topological phase transition is possible in ring-shaped spin interferometers away from the adiabatic limit: The transition is determined by the topology of the field texture through an effective Berry phase related to the winding parity of the spin eigenmodes around the poles in Bloch’s sphere [16]. Still, the experimental realization of the topological transition is challenging since the required in-plane Zeeman fields give rise to spin-induced dephasing [17] that ruins spin interference as the transition point is approached [18].

Recently, the possibility of spin reorientation by geometrical means has been considered after noticing that out-of-plane spin components develop by increasing the curvature of Rashba SO channels [19]. An early proposal for the geometric manipulation of electron spins was discussed in polygon loop interferometers [20], [21], where the polygon vertices act as strong spin-scattering centers that hinder the emergence of AC and geometric phases (by reducing the solid angle subtended by spin states during the propagation around the loop). This suggests that sharp curvatures could soften the stiffness of Rashba spin textures under the action of in-plane Zeeman fields, turning topological transitions possible at much weaker field strengths.

Here, we report transport simulations and experiments in square-shaped Rashba spin interferometers. Our simulations show that the topological properties of the spin eigenmodes (characterized by winding numbers) undergo a transition as an in-plane Zeeman field is applied. The topological transitions manifest as a sign reversal of spin interference leading to a distinctive
weak-(anti)localization pattern for weak Zeeman fields that contrasts with the case of ring-shaped interferometers. We demonstrate this response in a transport experiment with semiconductor square-shaped spin interferometers, establishing the existence of spin-texture topological transitions assisted by the polygonal geometry of the SO channels.

**1D transport simulation**

To clarify the role played by the spin interferometer’s shape, we resort to transport calculations in one-dimensional (1D) ballistic square and ring geometries including Rashba SO and in-plane Zeeman fields by means of the Landauer-Büttiker formulation [20]. The in-plane Zeeman field $B_{\text{in}}$ points along the direction aligned with the leads. The linear conductance by direct-path interference is calculated as a function of the Rashba SO frequency $\omega_R = \alpha k_F / h$ and the Zeeman frequency $\omega_Z = \mu_B B_{\text{in}} / h$, with $\alpha$ the Rashba SO strength, $k_F$ the Fermi wavenumber, and $\mu_B$ the Bohr magneton. The results are shown in Figs. 1(a) and 1(b), where the vertical and horizontal axes $k_Z P$ and $k_{SO} P$ correspond to the spin precession angles during spin propagation along the loop’s perimeter $P$ with $k_Z = \omega_Z / v_F = \mu_B B_{\text{in}} m^* / h^2 k_F$, $k_{SO} = \omega_R / v_F = \alpha m^* / h^2$, and $v_F$ the Fermi velocity. We find striking differences between the interference patterns of ring- and square-shaped interferometers:

(i) Vanishing in-plane Zeeman field: the AC oscillation period in a square loop is two times larger than in a ring loop. The AC phase for a ring (radius $r = P / 2\pi$) is given by $\pi \sqrt{1 + (k_{SO} P / \pi)^2}$ [22], corresponding to a $2\pi$-periodicity for large $k_{SO} P$ (with some deviations for small $k_{SO} P$ due to non-adiabatic spin dynamics, i.e., misalignment of spin and field textures). In contrast, the AC oscillation period of square loops is $4\pi$. This agrees with previous results showing that vertices act as spin-scattering centers leading to a strongly non-adiabatic spin dynamics that hinder the full development of AC and the Berry phases [20], even for large $k_{SO} P$.

(ii) Finite in-plane Zeeman field: a checkerboard pattern appears in the conductance of square loops as a function of $k_Z P$, indicating that the interference pattern is fully reversed by the in-plane Zeeman field. This periodic structure recalls the effect of an AB flux, suggesting that the in-plane Zeeman field has topological consequences by acting on the spin. This happens on a scale $k_Z P = \pi$, which is independent of the Rashba SO strength. In contrast, for ring loops the AC oscillations are shifted by the in-plane Zeeman field with no reversal of the interference pattern. This shift of the AC interference in rings has been experimentally observed and explained as a spin geometric phase effect [18].
We find that the checkerboard pattern of Fig. 1(a) is related to a topological aspect of the spin texture, viz., the winding number around the north pole of Bloch’s sphere shown in Fig. 1(e). This is better understood when considering the interference of time-reversal symmetric (TRS) paths, more relevant to experiments where disorder and sample averaging are determinant [see Figs. 1(c) and 1(d)]. Our simulations show that the TRS-path contribution to the conductance presents maxima only when the winding parity of the spin eigenmodes is odd and, consequently, the AC phase gathered by the spin in a round trip is sufficiently large to display weak antilocalization (WAL). Otherwise, the TRS paths contribute to weak localization (WL) by minimizing the conductance. The discontinuity of the Rashba SO field at the square’s corners turns adiabatic spin evolution impossible. This keeps the spin eigenstates away from the loop’s plane, developing complex spin textures that acquire equally complex phases. The AC phases are proportional to the projection of the spin textures on the radial SO field, naturally maximized for odd winding parities. The winding parity of strongly non-adiabatic spin textures is easily controlled by weak in-plane Zeeman fields, Fig. 1(e), producing the checkerboard pattern in the conductance, Figs. 1(a) and 1(c), that contrasts with the striped pattern shown by rings, Figs. 1(b) and 1(d), where strong in-plane Zeeman fields are necessary to produce a topological transition in the spin texture, Fig. 1(f) [16]. See Supplementary Material, Figs. S1-S4, for an extended discussion.

**Experiment and Discussion**

Our experimental setup consists of an array of Rashba square-shaped spin interferometers, which we use to investigate the topological transition induced by an in-plane Zeeman field. This configuration allows for a clear observation of the spin interference thanks to the ensemble averaging naturally provided by the sample.

We employed an InGaAs QW epitaxially grown on a InP (001) substrate. The detailed layer structure of the QW consist, from the bottom, of In$_{0.52}$Al$_{0.48}$As (200 nm, buffer layer)/In$_{0.52}$Al$_{0.48}$As (6 nm, carrier supply layer; Si-doping concentration of $4 \times 10^{16}$ cm$^{-3}$)/In$_{0.52}$Al$_{0.48}$As (15 nm, spacer layer)/In$_{0.53}$Ga$_{0.47}$As (2.5 nm, QW)/In$_{0.73}$Ga$_{0.27}$As (10 nm, QW)/In$_{0.53}$Ga$_{0.47}$As (2.5 nm, QW)/InP (5 nm, stopper layer)/In$_{0.52}$Al$_{0.48}$As (20 nm, barrier layer)/AlAs (1.5 nm, barrier layer)/In$_{0.52}$Al$_{0.48}$As (5 nm, cap layer). The carrier density dependence of the Rashba SO parameter $\alpha$ is obtained from the analysis of the beating patterns appearing in the gate voltage dependence of Shubnikov-de Haas oscillations. The Rashba SO parameter $\alpha$ is electrically controlled from $\alpha = -1.17$ peVm at $N_s = 2.0 \times 10^{12}$ cm$^{-2}$ ($V_g = -2$ V) to $\alpha = -3.62$ peVm at $N_s = 1.26 \times 10^{12}$ cm$^{-2}$ ($V_g = -5$ V).
A top-gate-attached 40×40 square loop array with square side length \( l = 700 \) nm was fabricated by electron beam lithography and reactive ion etching. A scanning electron microscope image of an array of 40 x 40 loops is shown in Fig. 2(a). The square loop array was covered with a 200-nm thick Al\(_2\)O\(_3\) insulator made by atomic layer deposition and a Cr/Au top gate electrode in order to tune the Rashba SO strength \( \alpha \) \([23],[24]\). All the measurements were performed at a temperature of 1.7 K. The in-plane magnetic field points along the squares diagonal direction.

We focus our study on the in-plane Zeeman field dependence of the Al’tshuler-Aronov-Spivak (AAS) \([25]\) oscillation amplitude due to TRS-path interference. It is notable that for TRS paths the phase contribution from the orbital part of the wave function is always constructive in the absence of perpendicular magnetic field \( B_\perp = 0 \) (WL). Hence, the amplitude of AAS oscillations at \( B_\perp = 0 \) as a function of top-gate voltages reflects exclusively the phase contribution from the spin part of the wave function. Thus we can evaluate the time-reversal AC spin-interference effect independently from the orbital phases, even at different top-gate voltages. The sign reversal of the AAS oscillation indicates that the constructive spin interference switches to destructive interference (WAL) or vice versa (WL restoration).

We measured the magnetoresistace (MR) by applying a weak perpendicular magnetic field \( B_\perp \) (few mT strength) as a function of the gate voltage \( V_g \) that controls the Rashba SO strength. A series of MR measurements was performed for different values of the in-plane Zeeman fields strength, running from \( B_{in} = 0.5 \) T to \( B_{in} = 2.5 \) T in steps of \( \Delta B_{in} = 0.5 \) T. Figure 2(b) shows the contour color plots of MR as a function of \( V_g \) at different field strengths \( B_{in} \). The insets of Fig. 2(b) contain the MR data at \( V_g = -3.6 \) V, showing the AAS oscillations with a period \( \Delta B_\perp = \left(\frac{\hbar}{2e}\right) l^2 \) because of the TRS-path interference appearing in the square loop array. The MR amplitude at \( B_\perp = 0 \) as a function of \( V_g \) corresponds to the AC spin interference \([26],[27]\). Although AC oscillations are not clear in Fig. 2(b), definite AC modulations by \( V_g \) are seen in Fig. S5 and Fig. S6. As discussed in Fig. 1(a), the AC oscillation period in the square loop is two times larger than the AC period of the ring-shaped spin interferometer in Fig. 1 (b). This is the reason why a whole period of the AC oscillation is not observed in the present sample ( -1.17 peV\( m < \alpha < -3.62 \) peV\( m \), corresponding to \( 0.68 < k_{SO}P(\pi) < 2.13 \)).

By increasing \( B_{in} \), the interference amplitudes weaken gradually due to spin-induced dephasing \([17]\) all over the gate voltage range. Still, a definite structure emerges as a function of \( B_{in} \). Around \( B_{in} = 1 \) T, the AAS amplitude vanishes at \( V_g = -3.6 \) V. Further increase in \( B_{in} (> 1.5 \) T) turns the AAS oscillations on again, but with a reversed AAS interference pattern. The sign reversal of
the AAS oscillations corresponds to the transition from a destructive spin interference (WAL) to a constructive one (WL). This is clearly seen in Fig. 3(a). It is interesting to compare this response with the corresponding one observed in a ring array, show in Fig. 3(b) for a fixed $V_g = -4.6$ V (corresponding to $\alpha = -2.9$ peVm). The sample (ring radius 600 nm) is the same one used in Ref. [18]. No inversion of the AAS oscillation pattern as a function of $B_{in}$ is observed in this case, so that the topological transition from WAL to WL never occurs in the studied gate voltage region. These results are consistent with the calculations shown in Fig. 1 (c) and (d) (checkerboard vs. striped patterns) based on the 1D ballistic model. The observed AAS oscillation reversal in the square loop array is attributed to the topological transition of spin interference as discussed in Fig. S2.

In a previous work, we demonstrated [16] that the topological transition in a ring happens when the in-plane Zeeman field equals effective SO field (namely, a topological transition in the spin texture requires a topological transition in field texture), which is given by $B_{eff} = 2\alpha k_F / g\mu_B$. The corresponding in-plane Zeeman field is estimated to be $B_{in} = 6.7$ T with $\alpha = -2.5$ peVm, $N_s = 1.6 \times 10^{12}$ cm$^{-2}$, and $g = 4$. The experimentally observed transition field in the square loop array is around $B_{in} = 1.5$ T, which is much weaker than expected in the ring-shaped interferometer and does not require a topological change in the hybrid SO/Zeeman field texture. This is the main result of this work.

2D numerical transport

The 1D ballistic model is useful to gain physical insight into the role played by the shape of SO interference loop. However, it is not so clear how the topological transition is affected by scattering and multi-mode transport. Therefore, we resort to two dimensional (2D) numerical simulations of disordered multi-mode square loops accounting for more realistic conditions. Here, we use the Kwant code [28] with a mean-free path of 1.2 $\mu$m, which is shorter that the square perimeter of 2.8 $\mu$m. This disorder is crucial to develop AAS interference paths [25]. We assume that the channel of the square loop includes 5-modes. The calculation details are described in [16]. We assume a Rashba SO strength of $\alpha = -2.0$ peVm, and g-factor of $g = 4$. Each side of the square loop is set to be 700 nm. These parameters are very similar to those in the InGaAs QW used in the present experiment. The numerical result shown in Fig. 4(a) indicates that the reversal of the AAS interference appears when the in-plane Zeeman field is around $B_{in} = 1.25$ T, reproducing the experimental results of Fig. 3 rather well.
We notice that the critical in-plane field producing the topological transition depends on the mean free path as shown in Fig. 4(b). This finding is compatible with previous results showing that disorder contributes to the development of non-adiabatic spin dynamics [29], boosting the effects of SO-field discontinuities at square’s corners.

Conclusions
The interference pattern found in our transport experiments with a Rashba square-loop array shows transitions from WAL to WL by introducing weak in-plane Zeeman fields. This experimental result matches the checkerboard pattern of the conductance as a function of the Rashba and Zeeman fields predicted by the theory, which has a topological interpretation in terms of spin-texture windings (fully correlated with WAL-WL zones). The transitions found in the square-shaped interferometer differ significantly from the striped pattern found in the ring-shaped ones, demonstrating the different structure of spin textures and phases. In Rashba rings, topological transitions in spin textures require large Zeeman fields (indeed, a topological transition in the field texture is needed). The situation is very different for Rashba squares, where small Zeeman fields can produce the transition due to the role played by the squares vertices as spin scattering centers. Additional sources of SO scattering as disorder appear to boost this effect.

Finally, we notice that the periodic (checkerboard) structure of the conductance and winding patterns for large Rashba strengths in squares [Figs. 1(a), 1(c), 1(e) and S2] suggests the existence of Brillouin-like zones for spin textures along the Rashba and Zeeman parameter spaces. This opens up the possibility of characterizing the reported topological transitions in terms of Chern numbers [30].

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Fig. 1 (a) Linear conductance by direct-path interference for a square loop as a function of the spin precession angles during spin propagation induced by Rashba SOI (x-axis) and in-plane Zeeman field (y-axis). (b) Linear conductance by direct-path interference for ring loop. Linear conductance by interference of time-reversal symmetric (TRS) paths for square loop (c) and for ring loop (d). Winding number around the north pole of Bloch’s sphere for square loop (e) and for ring loop (d).
Fig. 2 (a) A photo image of a 40×40 square loop array with square side length $l = 700$ nm. (b) Contour color plots of MR as a function of $V_g$ at different in-plane field strengths $B_{in}$. The insets of Fig. 2(b) contain the MR data at $V_g = -3.6$ V, showing the AAS oscillations.
Fig. 3 (a) AAS oscillations for a square loop array at $V_g = -3.6$ V ($\alpha = -2.5$ peVm) with different in-plane Zeeman fields $B_{\text{in}}$. The sign reversal of the AAS oscillations corresponds to the transition from a destructive spin interference (WAL) to a constructive one (WL). (b) AAS oscillations for a ring array with radius $r = 600$ nm at $\alpha = -2.9$ peVm. The transition from WAL to WL is not observed in the ring array.
Fig. 4 (a) AAS oscillations for a square loop with side length $l = 700$ nm calculated by using 2D numerical simulations (Kwant code). Here, we assume a mean-free path of 1.2 $\mu$m, Rashba SO strength of $\alpha = -2.0$ peVm, and g-factor of $g = 4$. (b) The critical in-plane field producing the topological transition depends on the mean free path. Other parameters are the same as in previous calculations.